Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO92 plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- · 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- · High commutation capability with sensitive gate
- High immunity to false turn-on by dV/dt
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- · Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

3. Applications

- General purpose motor control
- Small loads in washing machines
- Solenoid drivers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Absolute	maximum rating					
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 54 °C; Fig. 1; Fig. 2; Fig. 3	-	-	1	А
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G + T_j = 25 \text{ °C; } Fig. 7$	1	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2+ G-} $ $T_j = 25 \text{ °C; } Fig. 7$	1	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-} $ $T_i = 25 \text{ °C; } Fig. 7$	1	-	10	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		NI
2	G	gate		T2—T1
3	T1	main terminal 1	() () () () () () () () () () () () () (sym051

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA201-800E	TO92	BTA201-800E,412	Bulk	1000	SOT54	14-Nov-2013
BTA201-800E	TO92	BTA201-800E,112	Bulk	1000	SOT54	14-Nov-2013
BTA201-800E	TO92	BTA201-800E,116	Reel	2000	SOT54 wide pitch	14-Nov-2013
BTA201-800E/L01	TO92	BTA201-800E/L01EP	Bulk	500	SOT54	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA201-800E	201-8E

8. Limiting values

Table 5. Limiting valuesIn accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 54$ °C; Fig. 1; Fig. 2; Fig. 3	-	1	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; t_p = 20 ms; $T_{j(init)}$ = 25 °C; Fig. 4; Fig. 5	-	12.5	А
		full sine wave; t_p = 16.8 ms; $T_{j(init)}$ = 25 °C	-	13.7	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.78	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I _{GM}	peak gate current		-	2	А
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T _j	junction temperature		-40	125	°C

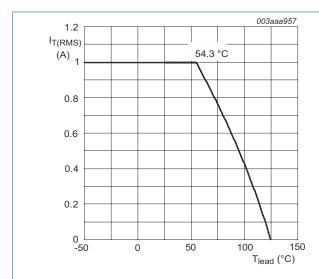
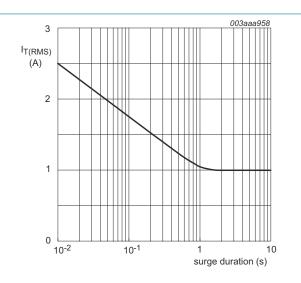
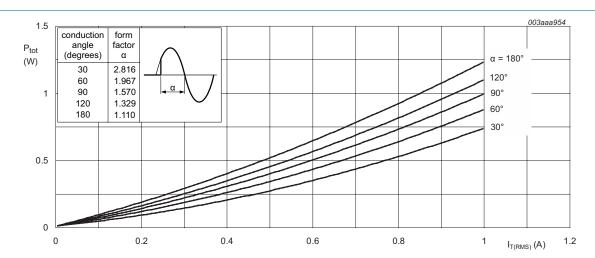


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



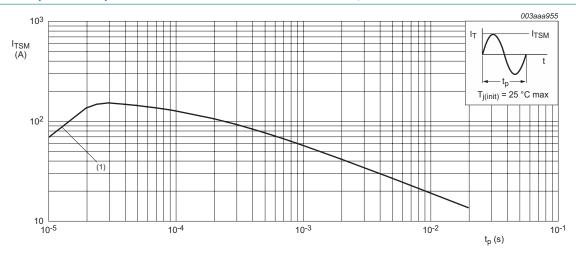
f = 50 Hz; T_{lead} = 54 °C Fig. 2. RMS on-state current as a function of surge duration; maximum values



 α = conduction angle

a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



 $t_p \le 20 \text{ ms}$; (1) $dI_T/dt \text{ limit}$

Fig. 4. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
		half cycle; Fig. 6	-	-	80	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	150	-	K/W

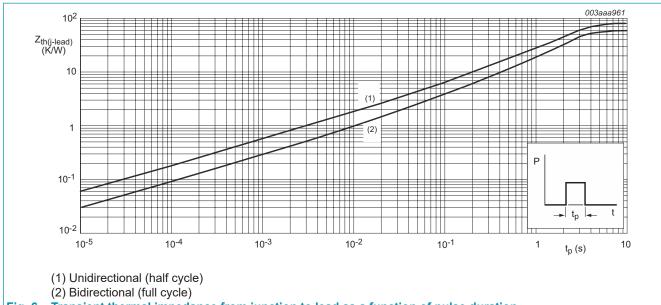
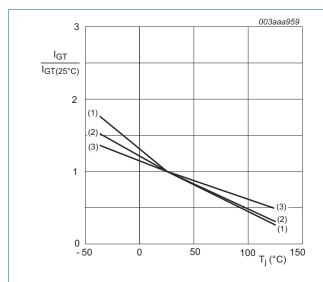


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	1	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2+ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	1	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	1	-	10	mA
I _L	latching current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	12	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	12	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	12	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C	0.2	0.3	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	600	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	2.5	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 1 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; gate open circuit}$	3.5	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

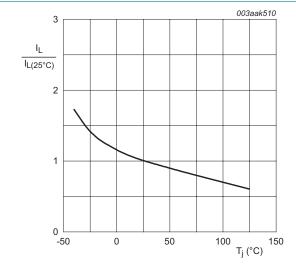


Fig. 8. Normalized latching current as a function of junction temperature

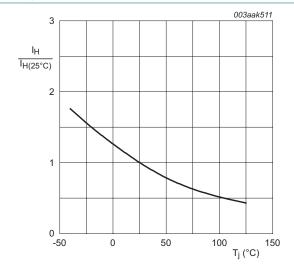
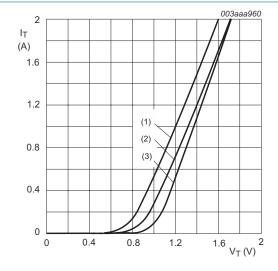


Fig. 9. Normalized holding current as a function of junction temperature



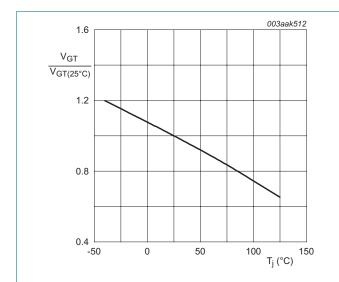
 V_o = 1.02 V; R_s = 0.358 Ω

(1) $T_j = 125$ °C; typical values (2) $T_j = 125$ °C; maximum values (3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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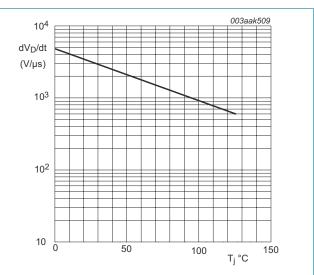
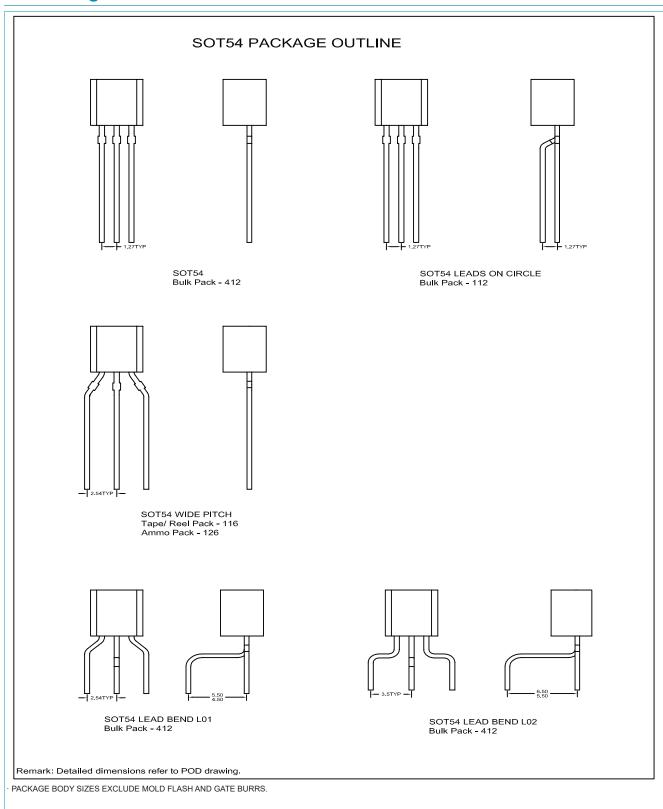
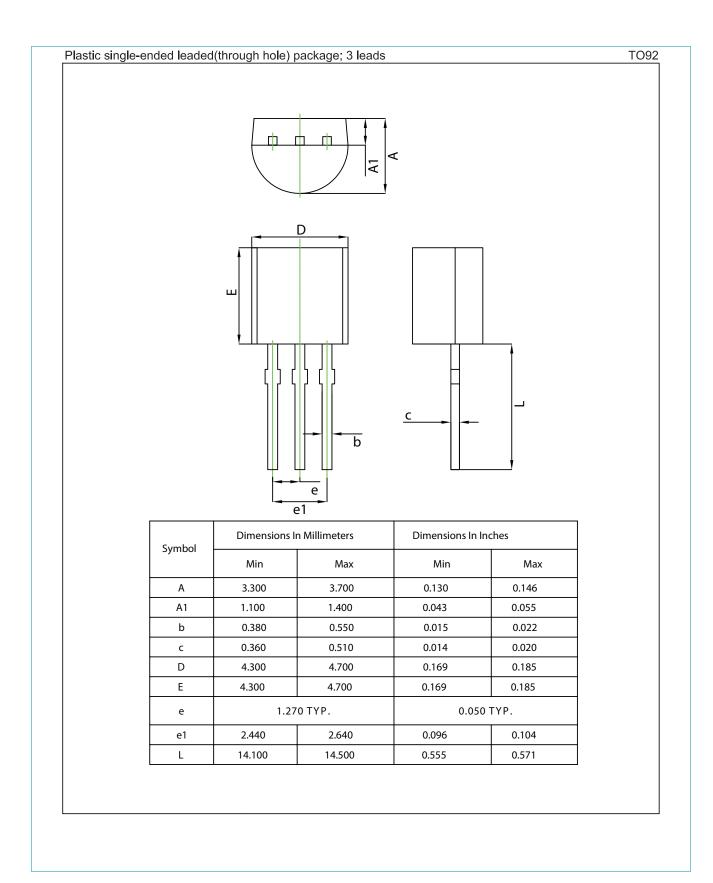


Fig. 11. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

11. Package outline





12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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13. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Characteristics	6
11. Package outline	9
12. Legal information	1 1
13. Contents	13

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